

AF/GAU 2813



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Gurtej Singh Sandhu et al.
Title: METHOD TO REDUCE FIXED CHARGE IN CVD OZONE DEPOSITED FILMS
Docket No.: 303.573US1 Serial No.: 08/636,069
Filed: April 22, 1996 Due Date: January 26, 1999
Examiner: Matthew Wipple Group Art Unit: 2813

Box AF

Assistant Commissioner for Patents
Washington, D.C. 20231

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We are transmitting herewith the following attached items (as indicated with an "X"):

JAN 28 1999

A return postcard.
 An Amendment and Response Under 37 C.F.R. § 1.116 (8 Pages).

GROUP 2100

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this Transmittal Letter and the paper, as described above, are being deposited in the United States Postal Service, as first class mail, in an envelope addressed to: Box AF, Assistant Commissioner for Patents, Washington, D.C. 20231, on this 25 day of January, 1999.

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(GENERAL)



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1-20-99
Robert
(AFM/AL)

EXPEDITED PROCEDURE - EXAMINING GROUP 2813

S/N 08/636,069

PATENT

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AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116

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In response to the final Office Action mailed October 26, 1998, please amend the application as follows to place the claims in better condition for appeal:

IN THE SPECIFICATION

On page 6, line 6, after "reaction" please remove "volume of gas; above the"

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IN THE CLAIMS

Please cancel claims 25-29 without prejudice.

1. (Twice amended) A chemical vapor deposition (CVD) process for depositing SiO₂ films on a substrate surface, said process comprising [the steps of]:
 - [(a)] disposing the substrate within a chemical vapor deposition reaction chamber;
 - [(b)] introducing a gas volume of SiO₂ precursors into said chamber;
 - [(c)] admitting a gas volume of ozone into the chamber;
 - [(d)] illuminating, with a source of high intensity light, the volume of gas located within [a chemically reactive distance of the substrate assembly surface,] the reaction chamber without [illuminating] directing the high intensity light at the substrate assembly.